

P-CHANNEL ENHANCEMENT MODE POWER MOSFET

MTP9435Q8

Description

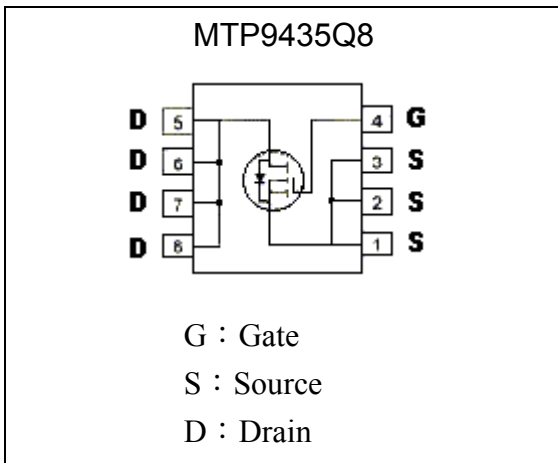
The MTP9435Q8 is a P-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness.

The SOP-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

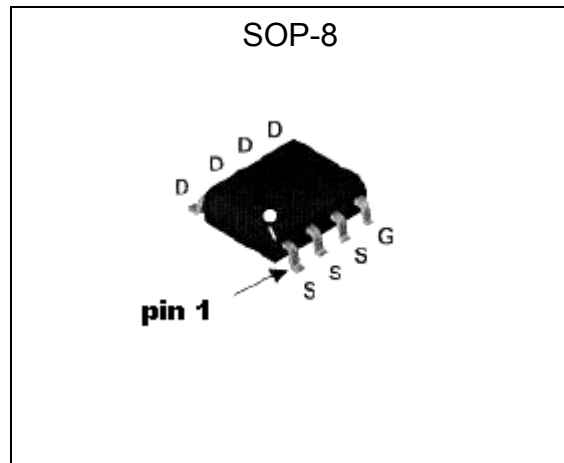
Features

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Pb-free package

Equivalent Circuit



Outline





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Breakdown Voltage	BVDSS	-30	V
Gate-Source Voltage	VGS	±20	V
Continuous Drain Current @TA=25°C	ID	-5.3	A
Continuous Drain Current @TA=70°C	ID	-4	A
Pulsed Drain Current (Note)	IDM	-20	A
Total Power Dissipation @ TA=25°C	Pd	2.5	W
Linear Derating Factor		0.02	W/°C
Operating Junction Temperature	Tj	-55~+150	°C
Storage Temperature	Tstg	-55~+150	°C
Thermal Resistance, Junction-to-Ambient	Rth,ja	50	°C/W

Note : Pulse width limited by safe operating area.

Electrical Characteristics (Ta=25°C)

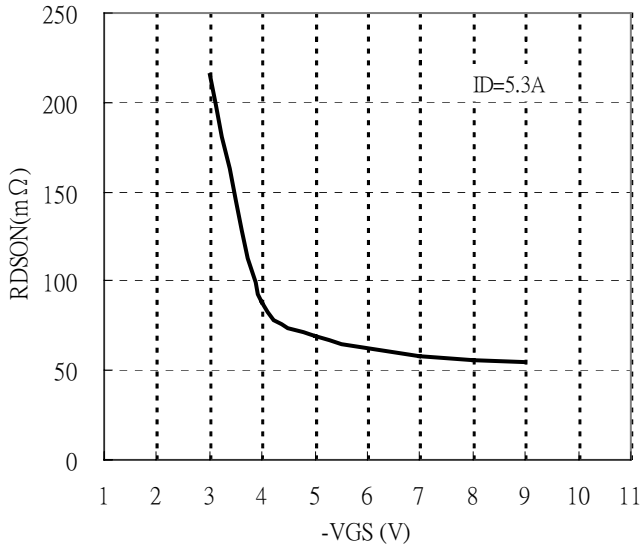
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVDSS	-30	-	-	V	VGS=0, ID=-250µA
VGS(th)	-1	-1.5	-3	V	VDS=VGS, ID=-250µA
IGSS	-	-	±100	nA	VGS=±20V, VDS=0
IDSS	-	-	-1	µA	VDS=-24V, VGS=0, Tj=25°C
*RDS(ON)	-	75	90	mΩ	ID=-4.2A, VGS=-4.5V
	-	50	60		ID=-5.3A, VGS=-10V
*GFS	4	7	-	S	VDS=-15V, ID=-5.3A
Ciss	-	551.57	-	pF	VDS=-15V, VGS=0, f=1MHz
Coss	-	90.96	-		
Crss	-	60.79	-		
*td(ON)	-	10.8	-	ns	VDS=-15V, ID=-1A, VGS=-10V, RGEN=6Ω, RD=15Ω
tr	-	2.33	-	ns	
td(OFF)	-	22.53	-	ns	
tf	-	3.87	-	ns	
*Qg	-	9.52	-	nC	VDS=-15V, ID=-5.3A, VGS=-10V,
Qgs	-	3.43	-	nC	
Qgd	-	1.71	-	nC	
ISD	-	-	-1.9	A	
*VSD	-	-	-1.3	V	VGS=0V, ISD=-5.3A

*Pulse Test : Pulse Width ≤380µs, Duty Cycle≤2%

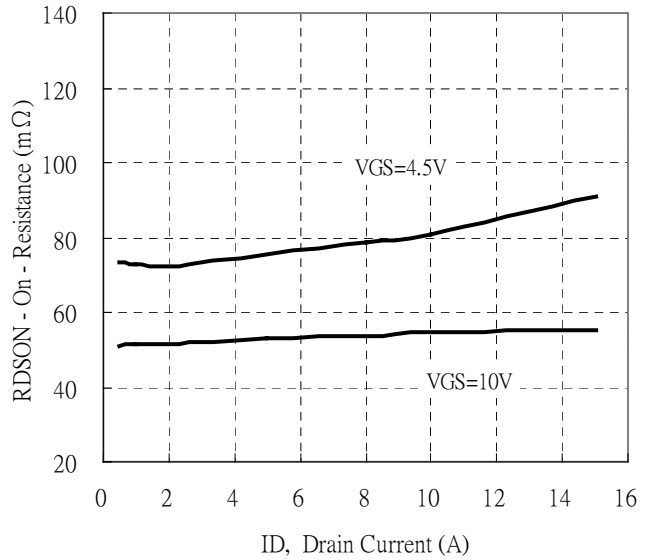


Characteristic Curves

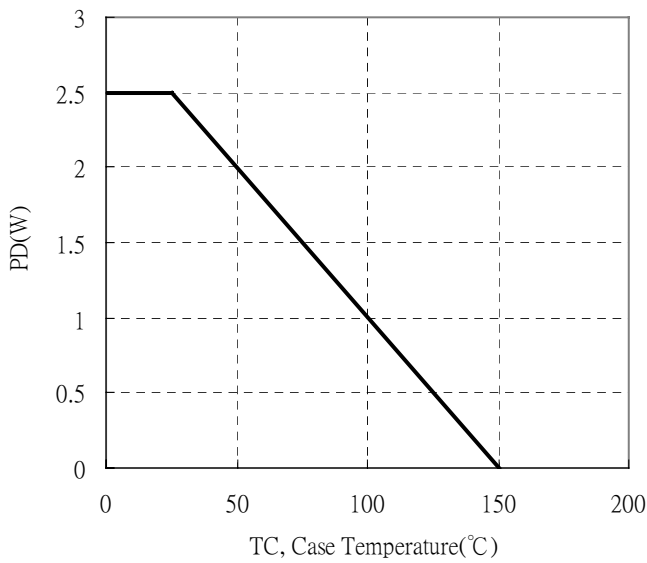
On-Resistance vs Gate Voltage



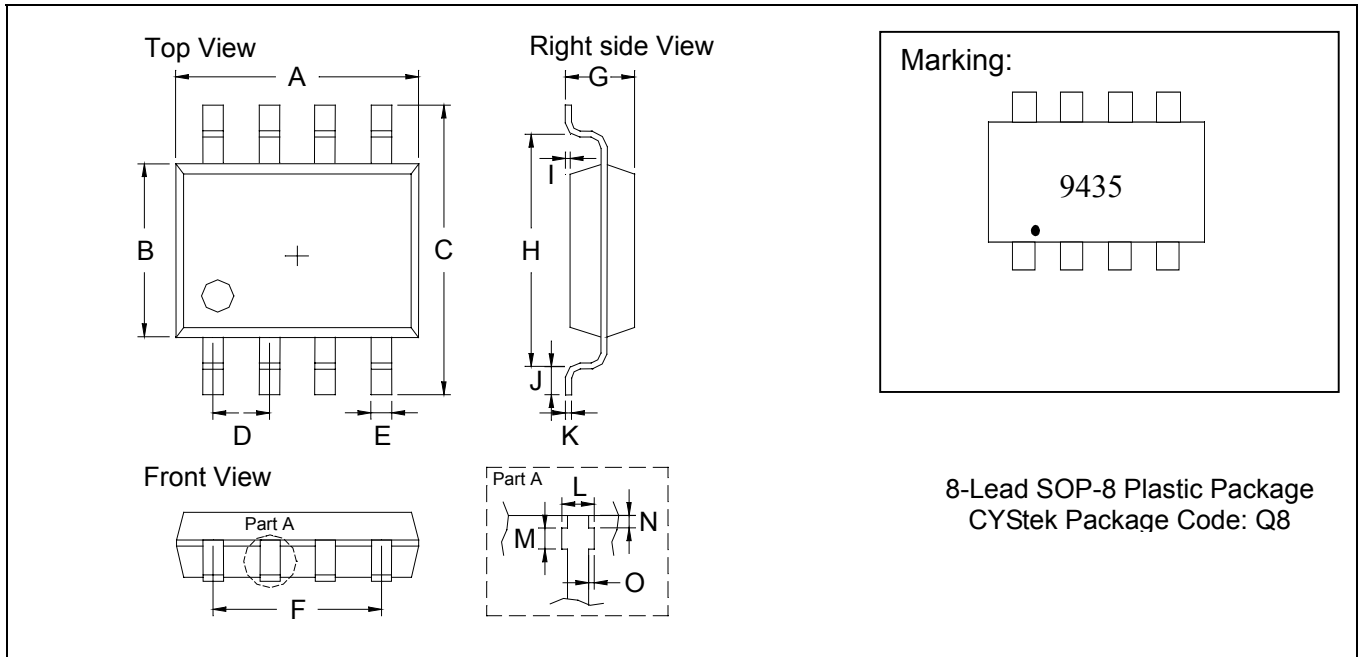
Drain-Source On Resistance



Typical Power Dissipation



SOP-8 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1909	0.2007	4.85	5.10	I	0.0019	0.0078	0.05	0.20
B	0.1515	0.1555	3.85	3.95	J	0.0118	0.0275	0.30	0.70
C	0.2283	0.2441	5.80	6.20	K	0.0074	0.0098	0.19	0.25
D	0.0480	0.0519	1.22	1.32	L	0.0145	0.0204	0.37	0.52
E	0.0145	0.0185	0.37	0.47	M	0.0118	0.0197	0.30	0.50
F	0.1472	0.1527	3.74	3.88	N	0.0031	0.0051	0.08	0.13
G	0.0570	0.0649	1.45	1.65	O	0.0000	0.0059	0.00	0.15
H	0.1889	0.2007	4.80	5.10					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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